

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	11/898583	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L2	1	10/596573	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L3	43243	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L4	69244	passivation near (layer\$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L5	284100	(contact or conductor or electrode) near (plug\$1 or hole\$1 or via\$1 or through-hole\$1 or (through near hole\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L6	532613	(wiring or metal or conductor) near (layer \$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L7	816	L3 and L4 and L5 and L6	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L8	680	(257/370).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L9	645	(257/378).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L10	4498	(257/758).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L11	3478	(257/774).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22

L12	871	(257/775).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L13	899	(257/776).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L14	39	(257/E27.109).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L15	53	(257/E29.221).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L16	133	(257/E25.01).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L17	1043	(257/E25.011).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L18	30	(257/E25.014).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L19	713	(257/E25.016).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L20	47	(257/E25.024).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L21	183	(257/E25.026).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L22	2078	(257/E23.145).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L23	5	US-4933297-\$.D.I.D. OR US-5563433-\$. D.I.D. OR US-5714793-\$.D.I.D. OR US- 6157068-\$.D.I.D. OR US-20020050627-\$. D.I.D. OR DE-20030327-\$.D.I.D.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/11/18 15:22
L24	1	US-20020104995-\$.D.I.D.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/11/18 15:22
L25	93	((ZHONG-XI'ANG) near2 (HE)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L26	22	((BRADLEY) near2 (ORNER)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L27	38	((VI DHYA) near2 (RAMACHANDRAN)). INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L28	67	((ALVIN) near2 (JOSEPH)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L29	45	((STEPHEN) near2 ("ST ONGE")).INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L30	79	((PING-CHUAN) near2 (WANG)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/11/18 15:22
L31	0	("23or24or25or26or27or28").PN.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L32	304	L25 or L26 or L27 or L28 or L29 or L30	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L33	2	("2002/0076874").URFN.	USPAT	ADJ	ON	2009/11/18 15:22

L34	43243	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L35	69244	passivation near (layer\$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L36	284100	(contact or conductor or electrode) near (plug\$1 or hole\$1 or via\$1 or through-hole\$1 or (through near hole\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L37	532613	(wiring or metal or conductor) near (layer \$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L38	816	L34 and L35 and L36 and L37	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L39	738	L38 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L40	680	(257/370).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L41	645	(257/378).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L42	4498	(257/758).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L43	3478	(257/774).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L44	871	(257/775).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L45	899	(257/776).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L46	39	(257/E27.109).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L47	53	(257/E29.221).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L48	133	(257/E25.01).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L49	1043	(257/E25.011).OCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22

L50	713	(257/E25.016).CQLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L51	47	(257/E25.024).CQLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L52	183	(257/E25.026).CQLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L53	2078	(257/E23.145).CQLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L54	12712	L40 or L41 or L42 or L43 or L44 or L45 or L46 or L47 or L48 or L49 or L50 or L51 or L52 or L53	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L55	9589	L54 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L56	954	L55 and (BiCMOS or (bipolar same (FET or (field near effect near transistor))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L57	1408	L55 and (passivation near (layer\$1 or film \$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L58	3801	L55 and ((contact or conductor or electrode) near (plug\$1 or hole\$1 or via \$1 or through-hole\$1 or (through near hole\$1)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L59	5690	L55 and ((wiring or metal or conductor) near (layer\$1 or film\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L60	48	L56 and L57 and L58 and L59	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L61	394	multi near2 (layer\$1 or level) near2 metal near2 interconnect	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22

L62	319	L61 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L63	481	vertical near2 bipolar same (fet or (field near effect near transistor))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L64	424	L63 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L65	3372	vertical near2 bipolar	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L66	2763	L65 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L67	751	L66 and mosfet	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L68	541	L67 not L64	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L69	541	L68 not L62	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L70	537	L68 not L39	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L71	537	L70 not L60	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22

L72	0	("2009/0039522").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L73	0	("2009/0039522").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L74	1	("20090050971").PN	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L75	1	11/958773	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L76	0	(11/958773).APP	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L77	0	(11/840604).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L78	1	11/840604	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L79	1	11/523566	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L80	15	("63999993").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L81	9	("6979884").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L82	0	("7534679").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L83	0	("7466010").URPN	USPAT	ADJ	ON	2009/11/18 15:22
L84	0	10/596573	USPAT	ADJ	ON	2009/11/18 15:22
L85	1	10/596573	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L86	1	11/693830	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L87	680	(257/370).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L88	645	(257/378).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L89	4498	(257/758).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22

L90	3478	(257/774).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L91	871	(257/775).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L92	899	(257/776).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L93	39	(257/E27.109).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L94	53	(257/E29.221).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L95	133	(257/E25.01).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L96	1043	(257/E25.011).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L97	713	(257/E25.016).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L98	47	(257/E25.024).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L99	183	(257/E25.026).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L100	2078	(257/E23.145).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 15:22
L101	12712	L87 or L88 or L89 or L90 or L91 or L92 or L93 or L94 or L95 or L96 or L97 or L98 or L99 or L100	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L102	9589	L101 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L103	954	L102 and (BICMOS or (bipolar same (FET or (field near effect near transistor))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 15:22
L104	20	("5015594" "5296391" "5391503" "5443994" "5523242").PN. OR ("6399993").URFN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/11/18 15:22
S1	1	11/898583	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 12:44
S2	1	10/596573	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 12:45

S3	41395	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S4	65714	passivation near (layer\$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S5	273227	(contact or conductor or electrode) near (plug\$1 or hole\$1 or via\$1 or through-hole\$1 or (through near hole\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:13
S6	513333	(wiring or metal or conductor) near (layer \$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:14
S7	766	S3 and S4 and S5 and S6	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:45
S8	670	(257/370).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:46
S9	635	(257/378).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:46
S10	4369	(257/758).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S11	3323	(257/774).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S12	847	(257/775).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S13	866	(257/776).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S14	38	(257/E27.109).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S15	53	(257/E29.221).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:47
S16	128	(257/E25.01).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S17	1040	(257/E25.011).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S18	25	(257/E25.014).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S19	708	(257/E25.016).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:48
S20	47	(257/E25.024).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49

S21	180	(257/E25.026).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49
S22	2020	(257/E23.145).CQLS.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:49
S23	5	US-4933297-\$.DID. OR US-5563433-\$. DID. OR US-5714793-\$.DID. OR US- 6157068-\$.DID. OR US-20020050627-\$. DID. OR DE-20030327-\$.DID.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/05/19 13:50
S24	1	US-20020104995-\$.DID.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/05/19 13:50
S25	85	((ZHONG-XIANG) near2 (HE)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:54
S26	20	((BRADLEY) near2 (ORNER)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:54
S27	37	((VI DHYA) near2 (RAMACHANDRAN)). INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:54
S28	59	((ALVIN) near2 (JOSEPH)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:54
S29	44	((STEPHEN) near2 ("ST ONGE")).INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:55
S30	63	((PING-CHUAN) near2 (WANG)).INV.	US-PGRUB; USPAT	ADJ	ON	2009/05/19 13:55
S31	0	("23or24or25or26or27or28").FN.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 13:58
S32	269	S25 or S26 or S27 or S28 or S29 or S30	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 13:59
S33	2	("2002/0076874").URFN.	USPAT	ADJ	ON	2009/05/19 14:34
S34	41395	BiCMOS or (bipolar same (FET or (field near effect near transistor)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S35	65714	passivation near (layer\$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S36	273227	(contact or conductor or electrode) near (plug\$1 or hole\$1 or via\$1 or through- hole\$1 or (through near hole\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S37	513333	(wiring or metal or conductor) near (layer \$1 or film\$1)	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28

S38	766	S34 and S35 and S36 and S37	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S39	698	S38 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 19:28
S40	670	(257/370).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S41	635	(257/378).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S42	4369	(257/758).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S43	3323	(257/774).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S44	847	(257/775).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S45	866	(257/776).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S46	38	(257/E27.109).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S47	53	(257/E29.221).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S48	128	(257/E25.01).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S49	1040	(257/E25.011).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S50	708	(257/E25.016).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S51	47	(257/E25.024).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S52	180	(257/E25.026).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S53	2020	(257/E23.145).CCL.S	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/19 20:56
S54	12350	S40 or S41 or S42 or S43 or S44 or S45 or S46 or S47 or S48 or S49 or S50 or S51 or S52 or S53	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S55	9556	S54 and (@pd<="20031216" or @ad<="20031216" or @rlad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56

S56	952	S55 and ((BiCMOS or (bipolar same (FET or (field near effect near transistor))))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S57	1398	S55 and ((passivation near (layer\$1 or film \$1)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:56
S58	3784	S55 and ((contact or conductor or electrode) near (plug\$1 or hole\$1 or via \$1 or through-hole\$1 or (through near hole\$1)))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:57
S59	5670	S55 and ((wiring or metal or conductor) near (layer\$1 or film\$1))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:57
S60	48	S56 and S57 and S58 and S59	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 20:58
S61	378	multi near2 (layer\$1 or level) near2 metal near2 interconnect	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:03
S62	317	S61 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:03
S63	471	vertical near2 bipolar same (fet or (field near effect near transistor))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:28
S64	420	S63 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:28
S65	3289	vertical near2 bipolar	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37

S66	2744	S65 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S67	738	S66 and mosfet	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S68	531	S67 not S64	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S69	531	S68 not S62	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:37
S70	527	S68 not S39	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:38
S71	527	S70 not S60	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/19 21:38
S72	0	("2009/0039522").URPN.	USPAT	ADJ	ON	2009/05/19 21:47
S73	0	("2009/0039522").URPN.	USPAT	ADJ	ON	2009/05/19 21:47
S74	1	("20090050971").PN.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/20 10:08
S75	0	11/958773	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 11:03
S76	0	(11/958773).APP.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/20 11:03
S77	0	(11/840604).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/05/20 20:33
S78	1	11/840604	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 20:33

S79	1	11/523566	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/20 20:59
S80	14	("6399993").URPN	USPAT	ADJ	ON	2009/05/21 13:20
S81	7	("6979884").URPN	USPAT	ADJ	ON	2009/05/21 13:22
S82	0	("7534679").URPN	USPAT	ADJ	ON	2009/05/21 13:23
S83	0	("7466010").URPN	USPAT	ADJ	ON	2009/05/21 13:23
S84	0	10/596573	USPAT	ADJ	ON	2009/05/21 13:27
S85	1	10/596573	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/21 13:27
S86	1	11/693830	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/05/21 17:13
S87	680	(257/370).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S88	645	(257/378).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S89	4498	(257/758).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S90	3478	(257/774).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S91	871	(257/775).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S92	899	(257/776).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S93	39	(257/E27.109).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S94	53	(257/E29.221).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S95	133	(257/E25.01).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S96	1043	(257/E25.011).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S97	713	(257/E25.016).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S98	47	(257/E25.024).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S99	183	(257/E25.026).CCLS	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36

S100	2078	(257/E23.145).CCL.S.	US-PGRUB; USPAT; USOCR	OR	OFF	2009/11/18 12:36
S101	12712	S87 or S88 or S89 or S90 or S91 or S92 or S93 or S94 or S95 or S96 or S97 or S98 or S99 or S100	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 12:36
S102	9589	S101 and (@pd<="20031216" or @ad<="20031216" or @riad<="20031216")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 12:36
S103	954	S102 and (BICMOS or (bipolar same (FET or (field near effect near transistor))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/11/18 12:36
S104	20	("5015594" "5296391" "5391503" "5443994" "5523242").PN. OR ("6399993").URFN.	US-PGRUB; USPAT; USOCR	ADJ	ON	2009/11/18 12:40

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L105	0	("Coplanar.clm.and(passivat \$4near1layer).clm. ").PN.	UPAD	OR	OFF	2009/11/18 16:54
L106	0	Coplanar.clm. and (passivat \$4near1layer).clm.	USPAT; UPAD	ADJ	ON	2009/11/18 16:54
L107	108	Coplanar.clm. and (passivat\$4 near1 layer).clm.	USPAT; UPAD	ADJ	ON	2009/11/18 16:55

11/ 18/ 2009 5:04:38 PM

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INTEGRATION WITH REDUCED CONTACT HEIGHT.wsp